Atomistic simulations of electronic transport in organic nanostructures

(Role of incoherent transport in molecular wires)

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Why Organics ?



Versatile Easy to produce Easy to interface with the bio-world Building blocks for complex structures

Organics for:

- Transistors
- Sensor
- Memories
- Field emission devices
- Mechanical components



Carbon Nanotubes



U ToVegeta

Molecular Devices



initial write. read erase Aн Acc. Au O₅N O_2N O_yN O₂N NH₂ high σ high σ low of low o V = 0 $\mathbf{V} = \mathbf{V} +$ V > 0 $\mathbf{V} = \mathbf{V}_{\mathbf{v}}$



M. Reed *et al*, APL 78, 3735 (2001) J.M. Tour *et al*, APL 82, 645 (2003)



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HP - Cross-bar Memories



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The DFTB approach I

[Porezag et al. Phys. Rev. B 51, 12947 (1995)]

LCAO expansion of the wave-function

$$\psi_i(\vec{r}) = \sum_{\nu} C_{\nu i} \phi_{\nu}(\vec{r} - \vec{R}_k) \qquad \sum_{\nu} C_{\nu i} (H_{\mu\nu} - \varepsilon_i S_{\mu\nu}) = 0 \quad \forall \mu, i$$

The Hamiltonian matrix elements are obtained as following:

1) Creation of (pseudo)atomic orbitals fn by selfconsistent solution of the atomic Kohn-Sham eq.

2) Calculation of the matrix elements

$$S_{\mu\nu} = \langle \phi_{\mu} | \phi_{\nu} \rangle$$

$$H_{\mu\nu} = \langle \phi_{\mu} | \hat{H} | \phi_{\nu} \rangle$$

$$= \begin{cases} \langle \phi_{\mu}^{A} | \hat{T} + V_{0}^{A} + V_{0}^{B} | \phi_{\nu}^{B} \rangle & A \neq B \\ \varepsilon_{\mu}^{free \ atom} & \mu = \nu \\ 0 & \text{otherwise} \end{cases}$$

$$V_{0} = V^{LDA} [\eta_{compressed}(r)]$$

3) Determination of the short-range core

$$V_{core}(R) = E_{tot}^{scf-LDA}(R) - E_{bs}^{DFTB}(R)$$

$$V_{core}(R) = \begin{cases} \sum_{n=2}^{N_p} d_n (R_c - R)^n & R < R_c \\ 0 & R \ge R_c \end{cases}$$



The DFTB approach II

[Elstner, et al. Phys. Rev. B 58 (1998) 7260]

Atomistic simulations with an approximate DFT method:

$$\hat{H}\psi_k(\vec{r}) = E_k\psi_k(\vec{r})$$

$$E[n(\vec{r})] = T_0[n(\vec{r})] + E_{Hartree}[n(\vec{r})] + E_{XC}[n(\vec{r})]$$

2nd order expansion of LDA functional
$$E^{(2)} = \sum_i n_i \langle \psi_i | H_0 | \psi_i \rangle + \frac{1}{2} \sum_{\mu,\nu} \gamma_{\mu\nu} \Delta q_\mu \Delta q_\nu + E^{rep}$$





Non-equilibrium transport



Open Boundary conditions

Carriers do not equilibrate

How do we fill up the states ?

In the absence of scattering:

$$iG_{\mu\nu}^{<} = \rho_{\mu\nu}^{L}f_{L}(E) + \rho_{\mu\nu}^{R}f_{R}(E)$$

$$\rho_{\mu\nu} = \frac{1}{2\pi i} \int dE \ G_{\mu\nu}^{<}(E) \quad \text{Density Matrix}$$



- Green's function approaches are numerically stable
- Inclusion of scattering (e-ph, e-e, etc) by self-energy functions.

NEGF + DFTB = gDFTB



A. Pecchia, A. Di Carlo, **Rep Prog Phys 67**, (2004) A. Pecchia *et al.*, *Introd. Mol. Elect.*, Springer, NY (2005)





SAMs of dithio-phenylene





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INNIVE

IV Characteristics



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The ICODE HUB

INTERNET COMPUTING ON DEMAND



Non-equilibrium scattering



Electron- phonon

$$\delta \mathcal{H} = \sum_{\mu,\nu} \sum_{q} \gamma^{q}_{\mu\nu} C^{\dagger}_{\mu} C_{\nu} (a^{+}_{q} + a_{q})$$

The electron-phonon coupling Hamiltonian is derived by expanding to first order the TB-Hamiltonian with respect to the atomic positions.

$$\gamma^{q}_{\mu\nu} = \frac{\partial H_{\mu\nu}}{\partial \xi_{q}} - \sum_{\lambda,\sigma} H_{\mu\lambda} S^{-1}_{\lambda\sigma} \frac{\partial S_{\sigma\nu}}{\partial \xi_{q}} - \frac{\partial S_{\mu\sigma}}{\partial \xi_{q}} S^{-1}_{\sigma\lambda} H_{\lambda\mu}$$

 ξ_q is the collective displacement of the atoms along a vibrational mode. This quantity is quantized as a position operator



Self-energies

$$\sum_{\mathbf{k}-\mathbf{q},\ \omega-\omega'}^{\mathbf{q},\ \omega'} : \quad \Sigma_{\phi}^{<}(E) = \frac{i}{2\pi} \sum_{q} \gamma_{q}^{2} \int dE \, G^{<}(E-E^{'}) D_{q}^{<}(E^{'})$$
Approximation for the phonon self-energy:
$$\operatorname{Im}\{\Sigma_{\phi}^{r}\} = \frac{1}{2} \left(\Sigma_{\phi}^{<} - \Sigma_{\phi}^{>}\right) \qquad \operatorname{Re}\{\Sigma_{\phi}^{r}\} = 0$$

Self-consistent Born approx.

Dyson's equation:
$$G^{r}(E) = \frac{1}{E - H_0 - \Sigma_c^{r}(E) - \Sigma_{\phi}^{r}(E)}$$

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Tovagala

Kinetic equation: $G^{<}(E) = G^{r}(E)[\Sigma_{c}^{<}(E) + \Sigma_{\phi}^{<}(E)]G^{a}(E)$

A simple model



Self-consistent solution







Inelastic spectroscopy



Wang, Nano Letters, 5, 450 (2004)



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Kushmerick, Nano Letters, 4, 639 (2004)



Application to benzene



Inelastic peaks



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Power emitted

Power emitted is computed using:

$$W = \frac{2}{h} \int Tr[\Sigma_{\phi}^{<}(E)G^{>}(E) - \Sigma_{\phi}^{>}(E)G^{<}(E)]EdE$$







Power released at 0.4 V 11 nW

Power released at 1.0 V 33 nW





Au/octanethiol/Au



Pecchia et al., Nano Letters 4, 2125 (2004)







The power is mostly released in the C-C stretch modes





Comparison with our result



LINUVE

Opto 2

Limitations of DFT

Tunneling is usually calculated using DFT spectrum





In principle we should include corrections beyond DFT in order to address this problem. (Exact exchange, CI, TD-DFT, GW)





Correlations: GW

Screened electron-electron potential to include correlations beyond DFT(B)

$$\Sigma^{GW}(E) = \frac{i}{2\pi} \int G(E - E') W(E') dE' \qquad \blacksquare \qquad W(E) = \varepsilon^{-1}(E) V$$

Key approximation on products of DFTB AO wavefunctions:

$$\phi_{\mu}(r)\phi_{\nu}(r) \approx S_{\mu\nu}\left[\left|\phi_{\mu}(r)\right|^{2}+\left|\phi_{\nu}(r)\right|^{2}\right]$$

T.A. Niehaus et al., Cond-matt/0411024





Effect of QP Corrections



U ToVagata

Future Work

• Implement real part on the self-energy to account for polaronic formation

• Construct a model for phonon relaxations in order to study heat dissipation into the contacts.



